

**=> IFW: Scan as Doc Code: SRNT <=
 Doc Date:**

TC 3700 Inventor Search Program

See attached inventor searches for applications and/or patents to help resolve questions of overlapping subject matter. These searches are provided as an initial examination aid: examiners should perform updated or expanded PALM or EAST inventors searches as appropriate.

Serial Number: 10/536,878

**1.) See attached printout of inventors listed in
PALM**

**2.) See attached EAST Inventor Search
Printout shows Inventor search terms**

Day : Tuesday
Date: 5/9/2006
Time: 12:27:24

 **PALM INTRANET**

Inventor Information for 10/536878

Inventor Name	City	State/Country
NISHIZAWA, JUN-ICHI	MIYAGI	JAPAN
NISHIZAWA, JUN-ICHI	MIYAGI	JAPAN

[Appln Info](#)[Contents](#)[Petition Info](#)[Atty/Agent Info](#)[Continuity Data](#)[Foreign Data](#)[Inventors](#) , /Search Another: Application# or Patent# PCT / / or PG PUBS # Attorney Docket # Bar Code #

To go back use Back button on your browser toolbar.

[Back to PALM](#) | [ASSIGNMENT](#) | [OASIS](#) | [Home page](#)

US 20060054940 A1	20060316	Short channel insulated-gate static induction transistor and method of manufacturing the same	257/242	257/327	Kurabayashi; Toru et al.
US 20040178442 A1	20040916	Short channel insulated-gate static induction transistor and method om manufacturing the same	257/327	257/328; 257/329; 438/259; 438/270	Kurabayashi, Toru et al.
US 20010001952 A1	20010531	SEMICONDUCTOR CRYSTAL GROWTH APPARATUS	118/724		NISHIZAWA, JUNICHI et al.
US 6977406 B2	20051220	Short channel insulated-gate static induction transistor and method of manufacturing the same	257/302	257/327; 257/328; 257/329; 257/E29.262; 257/E29.274	Kurabayashi; Toru et al.
US 6585599 B1	20030701	Game system and computer readable storage medium with reduced waiting period between selection and start of action of player character	463/43	463/31	Horigami; Atsushi et al.
US 6464793 B1	20021015	Semiconductor crystal growth apparatus	118/725	118/724; 156/345.33; 156/345.43; 156/345.48; 156/345.5	Nishizawa; Junichi et al.
US 6398650 B1	20020604	Game system, game progress control method, and computer-readable storage medium with a stored game program	463/43	463/1; 463/23; 463/44	Horigami; Atsushi et al.
US 6334901 B1	20020101	Apparatus for forming semiconductor crystal	118/725	117/102	Nishizawa; Junichi et al.
US 6323832 B1	20011127	Color display device	345/83	313/500; 362/800; 40/427; 40/541	Nishizawa; Junichi et al.
US 5883406 A	19990316	High-speed and high-density semiconductor memory	257/264	257/296; 257/300; 257/315; 257/E27.075; 257/E29.243	Nishizawa; Jun-ichi
US 5808328 A	19980915	High-speed and high-density semiconductor memory	257/264	257/296; 257/E27.075	Nishizawa; Jun-ichi
US 5693139 A	19971202	Growth of doped semiconductor monolayers	117/89	117/102; 117/105;	Nishizawa; Junichi et al.

				117/93; 117/953; 117/954; 117/956; 257/E21.09; 257/E21.11; 257/E21.123; 257/E21.131	
US 5663582 A	19970902	High frequency static induction transistor having high output	257/136	257/135; 257/264; 257/266; 257/494; 257/E21.401; 257/E29.013; 257/E29.118; 257/E29.127; 257/E29.243	Nishizawa; Junichi et al.
US 5615954 A	19970401	Apparatus for measuring the dew point or frost point of a gas having low water content	374/17	374/20; 73/29.01	Nishizawa; Junichi et al.
US 5585654 A	19961217	Field effect transistor having saturated drain current characteristic	257/264	257/263; 257/266; 257/E29.059; 257/E29.243	Nishizawa; Jun-ichi
US 5557119 A	19960917	Field effect transistor having unsaturated drain current characteristic	257/264	257/263; 257/266; 257/E29.059; 257/E29.243	Nishizawa; Jun-ichi
US 5552623 A	19960903	Short channel mosfet with buried anti-punch through region	257/345	257/297; 257/407; 257/E23.115; 257/E27.086; 257/E29.055; 257/E29.154; 257/E29.158; 257/E29.16; 257/E29.243; 257/E29.255	Nishizawa; Jun-ichi et al.
US 5542373 A	19960806	Method of manufacturing GaAs single crystals	117/103	117/904; 117/92; 117/954; 427/509; 427/582; 427/584	Nishizawa; Junichi et al.
US 5532511	19960702	Semiconductor device	257/627	257/263;	Nishizawa;

A		comprising a highspeed static induction transistor		257/264; 257/268; 257/628; 257/E21.406; 257/E29.243; 257/E29.315	Jun-ichi et al.
US 5527733 A	19960618	Impurity doping method with adsorbed diffusion source	438/558	257/E21.148	Nishizawa; Junichi et al.
US 5525156 A	19960611	Apparatus for epitaxially growing a chemical compound crystal	118/715	118/708; 118/712; 427/10	Manada; Nobuaki et al.
US 5500079 A	19960319	Dry etching method	438/708	257/E21.222; 257/E21.349	Nishizawa; Jun-ichi et al.
US 5485017 A	19960116	Semiconductor device and method of manufacturing same	257/24	257/104; 257/136; 257/30; 257/38; 257/458; 257/46; 257/498; 257/523; 257/E21.362; 257/E21.365; 257/E29.194; 257/E29.331; 438/191; 438/192; 438/268	Nishizawa; Jun-ichi
US 5482371 A	19960109	Method and apparatus for measuring the dew point and/or frost point of a gas having low water content	374/20	374/17; 374/28; 73/29.01	Nishizawa; Junichi et al.
US 5475242 A	19951212	Notched insulation gate static induction transistor integrated circuit	257/136	257/155; 257/158; 257/205; 257/369; 257/392; 257/598; 257/E27.062	Nishizawa; Jun-ichi et al.
US 5463977 A	19951107	Method of and apparatus for epitaxially growing chemical compound crystal	117/85	117/105; 117/108; 117/86; 117/89	Manada; Nobuaki et al.
US 5443033 A	19950822	Semiconductor crystal growth method	117/86	117/103; 117/108;	Nishizawa; Junichi et al.

				117/89; 117/92; 117/93	
US 5426314 A	19950620	Insulated gate control static induction thyristor	257/136	257/120; 257/124; 257/125; 257/130; 257/131; 257/135; 257/144; 257/152; 257/273; 257/283; 257/E29.195; 257/E29.196	Nishizawa; Jun-ichi et al.
US 5384476 A	19950124	Short channel MOSFET with buried anti-punch through region	257/345	257/297; 257/407; 257/E23.115; 257/E27.086; 257/E29.055; 257/E29.154; 257/E29.158; 257/E29.16; 257/E29.243; 257/E29.255	Nishizawa; Jun-ichi et al.
US 5357361 A	19941018	Discriminating light-emitting optical apparatus	398/108	340/539.1; 340/691.6; 340/825.49; 398/106	Nishizawa; Jun-ichi
US 5341577 A	19940830	Drying method of and drying apparatus for powder and granular material	34/493	236/1E; 34/132; 34/551	Hashimoto; Iori et al.
US 5338389 A	19940816	Method of epitaxially growing compound crystal and doping method therein	117/89	117/953; 117/954; 117/955	Nishizawa; Jun-ichi et al.
US 5323029 A	19940621	Static induction device	257/136	257/132; 257/154; 257/162; 257/332; 257/334; 257/E27.052; 257/E29.196	Nishizawa; Jun-ichi
US 5323028 A	19940621	MOS composite static induction thyristor	257/136	257/262; 257/264; 257/265; 257/272;	Nishizawa; Jun-ichi et al.

				257/498; 257/E29.196; 327/438; 327/565; 327/566	
US 5296403 A	19940322	Method of manufacturing a static induction field-effect transistor	438/198	257/E21.406; 257/E29.243; 257/E29.315; 438/270	Nishizawa; Jun-ichi et al.
US 5294286 A	19940315	Process for forming a thin film of silicon	117/93	117/102; 117/89; 117/935; 438/925	Nishizawa; Junichi et al.
US 5254207 A	19931019	Method of epitaxially growing semiconductor crystal using light as a detector	117/86	117/954; 356/318; 356/632	Nishizawa; Jun-ichi et al.
US 5250148 A	19931005	Process for growing GaAs monocrystal film	117/93	117/954	Nishizawa; Junichi et al.
US 5246536 A	19930921	Method for growing single crystal thin films of element semiconductor	117/102	117/935; 257/E21.102	Nishizawa; Junichi et al.
US 5240685 A	19930831	Apparatus for growing a GaAs single crystal by pulling from GaAs melt	117/202	117/213; 117/900; 117/906	Nishizawa; Jun-ichi
US 5227647 A	19930713	Semiconductor switching device	257/136	257/119; 257/E29.196	Nishizawa; Jun-ichi et al.
US 5175598 A	19921229	Semiconductor switching device	257/107	257/136; 257/256; 257/264; 257/E29.196	Nishizawa; Jun-ichi et al.
US 5169795 A	19921208	Method of manufacturing step cut type insulated gate SIT having low-resistance electrode	438/586	257/E21.199; 257/E21.401; 257/E21.507; 257/E29.156; 257/E29.243; 257/E29.262; 438/270; 438/589	Nishizawa; Jun-ichi et al.
US 5117268 A	19920526	Thermionic emission type static induction transistor and its integrated circuit	257/27	257/192; 257/264; 257/E27.012; 257/E29.049; 257/E29.091; 257/E29.14; 257/E29.243	Nishizawa; Junichi et al.

US 5115287 A	19920519	Step-cut insulated gate static induction transistors and method of manufacturing the same	257/334	257/332; 257/E21.258; 257/E21.401; 257/E29.243	Nishizawa; Junichi et al.
US 5074954 A	19911224	Process and apparatus for growing compound semiconductor monocrystal	118/719	118/667; 118/725; 118/726; 148/33; 156/DIG.20; 257/E21.108	Nishizawa; Junichi
US 5065206 A	19911112	Photoelectric converting device with accumulating gate region	257/462	257/465; 257/E27.148	Nishizawa; Jun-Ichi et al.
US 5060029 A	19911022	Step cut type insulated gate SIT having low-resistance electrode and method of manufacturing the same	257/263	257/330; 257/413; 257/755; 257/E21.199; 257/E21.401; 257/E29.156; 257/E29.243; 257/E29.262	Nishizawa; Jun-ichi et al.
US 5052818 A	19911001	Method of and apparatus for measuring very low water content in gas	374/17	374/20; 73/29.01	Nishizawa; Junichi et al.
US 5038188 A	19910806	Insulated-gate type transistor and semiconductor integrated circuit using such transistor	257/136	257/369; 257/389; 257/E27.061; 257/E27.062; 257/E29.243; 257/E29.268	Nishizawa; Jun-ichi et al.
US 5035767 A	19910730	Process for growing compound semiconductor monocrystal	117/99	117/88; 117/904; 117/954; 118/715; 156/DIG.20; 257/E21.108	Nishizawa; Junichi
US 5027180 A	19910625	Double gate static induction thyristor	257/266	257/107; 257/136; 257/272; 257/623; 257/E29.059; 257/E29.196	Nishizawa; Jun-ichi et al.
US 5021936 A	19910604	PWM power converter using mixed bipolar and static induction transistors	363/41	363/132	Nishizawa; Jun-ichi et al.
US 5019876	19910528	Semiconductor photo-	257/147	257/E27.148;	Nishizawa;

A		electric converter		257/E31.079	Jun-ichi
US 5017991 A	19910521	Light quenchable thyristor device	257/114	257/117; 257/136; 257/257; 257/272; 257/462; 257/E29.047; 257/E29.048; 257/E29.059; 257/E29.196; 257/E29.212; 257/E31.071; 327/514; 327/564	Nishizawa; Jun-ichi et al.
US 5001535 A	19910319	Static induction type thyristor	257/169	257/136; 257/146; 257/156; 257/212; 257/487; 257/618; 257/656; 257/E29.02; 257/E29.037; 257/E29.059; 257/E29.126; 257/E29.195; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4994999 A	19910219	High-speed and high-density semiconductor memory	365/149	257/264; 257/266; 257/296; 257/E27.075; 257/E29.243	Nishizawa; Jun-ichi
US 4994872 A	19910219	Insulated gate static induction transistor and integrated circuit including same	257/337	257/333; 257/334; 257/346; 257/369; 257/E27.061; 257/E27.062; 257/E29.051; 257/E29.054; 257/E29.067; 257/E29.131; 257/E29.243; 257/E29.256	Nishizawa; Jun-ichi et al.
US 4985738 A	19910115	Semiconductor switching device	257/136	257/175; 257/218;	Nishizawa; Jun-ichi et al.

				257/66; 257/E29.196	
US 4984049 A	19910108	Static induction thyristor	257/136	257/155; 257/170; 257/172; 257/264; 257/266; 257/269; 257/E29.037; 257/E29.049; 257/E29.059; 257/E29.109; 257/E29.126; 257/E29.196; 257/E29.211	Nishizawa; Jun-ichi et al.
US 4975755 A	19901204	Optically controllable static induction thyristor device	257/114	257/136; 257/154; 257/432; 257/E29.037; 257/E29.059; 257/E29.195; 257/E29.196; 257/E31.072; 348/96	Nishizawa; Junichi
US 4975252 A	19901204	Semiconductor crystal growth apparatus	118/688	117/86; 117/89; 118/715; 118/724; 118/725; 422/110	Nishizawa; Junichi et al.
US 4968491 A	19901106	Apparatus for performing epitaxial growth of ZNSE crystal from melt thereof	118/407	117/59; 422/253	Nishizawa; Jun-ichi
US 4964023 A	19901016	Holder with semiconductor lighting device	362/100	362/116; 362/802; 70/277	Nishizawa; Junichi et al.
US 4956599 A	19900911	Power control apparatus	323/244	257/136; 323/902	Nishizawa; Jun-ichi et al.
US 4952996 A	19900828	Static induction and punching-through photosensitive transistor devices	257/257	257/448; 257/E27.148	Nishizawa; Jun-Ichi et al.
US 4939571 A	19900703	Insulated-gate type transistor and semiconductor integrated circuit using such transistor	257/408	257/409; 257/491; 257/E27.061; 257/E27.062;	Nishizawa; Jun-ichi et al.

				257/E29.243; 257/E29.268	
US 4935798 A	19900619	Static induction type thyristor	257/130	257/136; 257/155; 257/167; 257/E29.02; 257/E29.037; 257/E29.059; 257/E29.126; 257/E29.195; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4917757 A	19900417	Method of performing solution growth of ZnSe crystals	117/77	117/956; 148/33; 438/925; 438/971	Nishizawa; Jun-ichi
US 4914043 A	19900403	Method of making an integrated light-triggered and light-quenched static induction thyristor	438/59	257/136; 257/E27.128; 257/E29.037; 257/E29.196; 257/E31.072; 438/137	Nishizawa; Jun-ichi et al.
US 4909998 A	19900320	Apparatus for performing solution growth of group II-VI compound semiconductor crystal	117/223	117/900; 117/902; 117/906; 117/956; 117/958	Nishizawa; Jun-ichi
US 4903938 A	19900227	Micro flow control valve	251/61.5	251/129.16; 251/333; 251/359; 251/368	Nishizawa; Jun-ichi et al.
US 4891682 A	19900102	Solid state image pick-up device having a number of static induction transistor image sensors	257/258	257/229; 257/264; 257/445; 257/E27.148	Yusa; Atsushi et al.
US 4876580 A	19891024	Tunnel injection controlling type semiconductor device controlled by static induction effect	257/330	257/497; 257/E29.039; 257/E29.195; 257/E29.196; 257/E29.243; 257/E29.305	Nishizawa; Jun-ichi
US 4872044 A	19891003	Static induction type thyristor	257/136	257/156; 257/168; 257/E29.02; 257/E29.037; 257/E29.059; 257/E29.126;	Nishizawa; Jun-ichi et al.

				257/E29.195; 257/E29.196	
US 4870469 A	19890926	Tunnel injection type static transistor and its integrated circuit	257/367	257/330; 257/E27.012; 257/E29.039; 257/E29.049; 257/E29.091; 257/E29.14; 257/E29.243	Nishizawa; Junichi et al.
US 4870028 A	19890926	Method of making double gate static induction thyristor	438/137	257/136; 257/E29.059; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4866500 A	19890912	Integrated light-triggered and light-quenched static induction thyristor and making method thereof	257/114	257/115; 257/116; 257/136; 257/146; 257/257; 257/E27.128; 257/E29.037; 257/E29.196; 257/E31.072	Nishizawa; Jun-ichi et al.
US 4841350 A	19890620	Static induction photothyristor having a non-homogeneously doped gate	257/113	257/136; 257/655; 257/E29.048; 257/E29.196; 257/E29.211; 257/E29.212; 257/E31.038; 257/E31.071	Nishizawa; Jun-ichi
US 4837608 A	19890606	Double gate static induction thyristor and method for manufacturing the same	257/136	257/485; 257/E29.059; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4834831 A	19890530	Method for growing single crystal thin films of element semiconductor	117/93	117/935	Nishizawa; Junichi et al.
US 4831504 A	19890516	Holder with semiconductor lighting device	362/100	362/116; 362/184; 362/800; 70/456R	Nishizawa; Junichi et al.
US 4819058 A	19890404	Semiconductor device having a pn junction	257/103	257/609; 257/76; 257/77; 257/E21.464; 257/E21.465; 257/E21.467; 257/E33.019	Nishizawa; Jun-ichi

US 4816891 A	19890328	Optically controllable static induction thyristor device	327/474	257/114; 257/136; 257/E29.037; 257/E29.059; 257/E29.195; 257/E29.196; 257/E31.072; 327/438; 327/441; 327/515	Nishizawa; Junichi
US 4814843 A	19890321	Charge transfer device with pn junction gates	257/217	257/216; 257/221; 257/E29.228; 377/68	Nishizawa; Jun-ichi
US 4814839 A	19890321	Insulated gate static induction transistor and integrated circuit including same	257/329	257/264; 257/334; 257/E27.061; 257/E27.062; 257/E29.051; 257/E29.054; 257/E29.067; 257/E29.131; 257/E29.243; 257/E29.256	Nishizawa; Jun-ichi et al.
US 4811064 A	19890307	Static induction transistor and integrated circuit device using same	257/264	257/273; 257/E27.031; 257/E27.032; 257/E29.031; 257/E29.059; 257/E29.186; 257/E29.187; 257/E29.194	Nishizawa; Jun-Ichi et al.
US 4806321 A	19890221	Use of infrared radiation and an ellipsoidal reflection mirror	118/666	118/725; 257/E21.108; 427/248.1	Nishizawa; Junichi et al.
US 4799090 A	19890117	Tunnel injection controlling type semiconductor device controlled by static induction effect	257/106	257/263; 257/266; 257/279; 257/280; 257/E29.039; 257/E29.195; 257/E29.196; 257/E29.243; 257/E29.305	Nishizawa; Jun-ichi
US 4791396 A	19881213	Color image sensor	257/258	257/440; 257/E27.148;	Nishizawa; Jun-ichi et al.

				257/E31.079	
US 4783426 A	19881108	Method of making a Group II-VI compound semiconductor device by solution growth	117/79	117/83; 117/956; 117/958; 257/78; 257/E21.465; 257/E33.019; 438/22	Nishizawa; Jun-ichi
US 4772926 A	19880920	Insulated gate static induction type thyristor	257/136	257/156; 257/170; 257/E29.02; 257/E29.037; 257/E29.059; 257/E29.126; 257/E29.195; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4755856 A	19880705	Znse green light emitting diode	438/46	117/79; 117/956; 257/E33.019; 257/E33.022; 438/915; 438/917; 438/971	Nishizawa; Jun-ichi
US 4745374 A	19880517	Extremely-high frequency semiconductor oscillator using transit time negative resistance diode	331/96	331/107DP; 331/107R; 331/107T	Nishizawa; Jun-ichi et al.
US 4725873 A	19880216	Semiconductor imaging device	257/258	257/E27.148	Nishizawa; Junichi et al.
US 4725563 A	19880216	ZnSe green light emitting diode	117/74	117/83; 257/E33.019; 257/E33.022; 438/925	Nishizawa; Jun-ichi
US 4720735 A	19880119	Phototransistor having a non-homogeneously base region	257/462	257/463; 257/E31.038; 257/E31.069	Nishizawa; Jun-ichi
US 4719551 A	19880112	Optically controlled power converting apparatus	363/41	257/114; 257/124; 257/136; 323/207; 327/467; 327/564; 363/128; 363/129; 363/136; 363/137;	Nishizawa; Junichi et al.

				363/37	
US 4719499 A	19880112	Semiconductor imaging device	257/258	257/291; 257/749; 257/E27.148; 348/307	Nishizawa; Junichi et al.
US 4712122 A	19871208	Heterojunction gate ballistic JFET with channel thinner than Debye length	257/27	257/192; 257/264; 257/266; 257/272; 257/E27.012; 257/E29.049; 257/E29.091; 257/E29.14; 257/E29.243; 438/191; 438/193	Nishizawa; Junichi et al.
US 4700213 A	19871013	Multi-drain enhancement JFET logic (SITL) with complementary MOSFET load	257/262	257/264; 257/E27.032; 257/E27.059; 257/E29.194	Nishizawa; Jun-ichi et al.
US 4692789 A	19870908	Semiconductor apparatus	257/664	257/136; 257/688; 257/689; 257/724; 257/E21.506	Nakamura; Yoshio et al.
US 4692194 A	19870908	Method of performing solution growth of a GaAs compound semiconductor crystal layer under control of conductivity type thereof	117/56	117/61; 117/67; 117/907; 117/954; 257/E21.117; 438/915	Nishizawa; Jun-ichi
US 4686555 A	19870811	Solid state image sensor	257/446	257/113; 257/258; 257/291; 257/E27.148; 257/E29.243; 257/E31.079; 257/E31.085	Yusa; Atsushi et al.
US 4685979 A	19870811	Method of manufacturing a group II-VI compound semiconductor device having a pn junction	438/501	117/56; 117/67; 257/E21.464; 257/E21.465; 257/E21.467; 257/E33.019; 438/22	Nishizawa; Jun-ichi
US 4684968	19870804	JFET imager having light	257/258	257/291;	Ohta;

A		sensing inversion layer induced by insulator charge		257/446; 257/E27.148	Yoshinori et al.
US 4684966 A	19870804	Static induction transistor photodetector having a deep shielding gate region	257/258	257/264; 257/E27.131; 257/E27.148; 257/E29.059	Nishizawa; Junichi et al.
US 4673985 A	19870616	Semiconductor image sensor	348/307	257/258; 257/261; 257/264; 257/296; 257/E27.148	Nishizawa; Jun-ichi
US 4673961 A	19870616	Pressurized contact type double gate static induction thyristor	257/181	257/136; 257/727; 257/E23.078; 257/E23.187; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4668306 A	19870526	Method of manufacturing a semiconductor device having unhomogeneous distribution of impurity concentration	438/379	257/480; 257/E21.152; 257/E21.341; 257/E21.473; 257/E29.109; 257/E29.338; 438/508; 438/522	Nishizawa; Jun-ichi
US 4660062 A	19870421	Insulated gate transistor having reduced channel length	257/345	257/384; 257/E21.426; 257/E21.429; 257/E21.43; 257/E29.13; 257/E29.131; 257/E29.154; 257/E29.156; 257/E29.16; 257/E29.243; 257/E29.26	Nishizawa; Junichi et al.
US 4651180 A	19870317	Semiconductor photoelectric transducer	257/257	257/261; 257/264; 257/270; 257/E27.148; 257/E31.079; 257/E31.085	Nishizawa; Jun-ichi et al.
US 4651015 A	19870317	Semiconductor imaging device utilizing static induction transistors	250/208.1	257/258; 257/261; 257/264; 257/296; 257/E27.148;	Nishizawa; Junichi et al.

				348/307	
US 4644386 A	19870217	Integrated circuit employing insulated gate electrostatic induction transistor	257/339	257/400; 257/E27.061; 257/E27.062; 257/E27.086; 257/E29.155; 257/E29.156; 257/E29.158; 257/E29.243	Nishizawa; Junichi et al.
US 4641167 A	19870203	Semiconductor optoelectro transducer	257/257	257/136; 257/439; 257/E27.148; 257/E29.126; 257/E29.196; 257/E29.243; 257/E31.077; 257/E31.079	Nishizawa; Jun-chi
US 4631592 A	19861223	Semiconductor image sensor	348/307	257/113; 257/136; 257/E27.148	Nishizawa; Jun-ichi
US 4629901 A	19861216	Photo coupler with static induction transistor type detector	250/551	257/136; 257/E31.079; 257/E31.095; 257/E31.108; 257/E31.109	Nishizawa; Jun-ichi
US 4626916 A	19861202	Solid state image pickup device	348/307	257/225; 257/258; 257/263; 257/E27.148; 348/296	Mizoguchi; Toyokazu et al.
US 4623909 A	19861118	Semiconductor photodetector	257/446	257/113; 257/435; 257/513; 257/E27.148; 257/E31.079	Nishizawa; Jun-ichi et al.
US 4619811 A	19861028	Apparatus for growing GaAs single crystal by using floating zone	117/202	117/222; 117/954; 373/139; 373/148	Nishizawa; Jun-ichi
US 4619718 A	19861028	Method of manufacturing a Group II-VI semiconductor device having a PN junction	438/501	117/56; 117/906; 117/956; 117/958; 257/E21.464; 257/E21.465; 257/E21.467;	Nishizawa; Jun-ichi

				257/E33.019; 438/22; 438/918	
US 4616249 A	19861007	Solid state image pick-up element of static induction transistor type	257/446	257/113; 257/E27.148	Nishizawa; Jun-ichi et al.
US 4613881 A	19860923	Vertical semiconductor photoelectric transducer with improved separated gate structure	257/257	257/263; 257/270; 257/E29.059; 257/E29.243; 257/E31.079	Nishizawa; Jun-ichi
US 4608587 A	19860826	Semiconductor optoelectro transducer	257/258	257/136; 257/432; 257/466; 257/E27.148; 257/E29.126; 257/E29.196; 257/E29.243; 257/E31.077	Nishizawa; Jun-ichi
US 4608582 A	19860826	Semiconductor device having non-saturating I-V characteristics and integrated circuit structure including same	257/497	257/264; 257/378; 257/512; 257/521; 257/E21.546; 257/E21.549; 257/E21.572; 257/E27.031; 257/E27.032; 257/E29.194	Nishizawa; Jun-ichi
US 4603420 A	19860729	Optical integrated circuit	372/45.01	372/46.01; 372/50.1	Nishizawa; Junichi et al.
US 4596605 A	19860624	Fabrication process of static induction transistor and solid-state image sensor device	438/57	257/264; 257/266; 257/285; 257/E21.335; 257/E21.401; 257/E29.086; 257/E29.243; 257/E31.079; 438/186; 438/528; 438/87	Nishizawa; Junichi et al.
US 4593320 A	19860603	Two-dimensional solid-state image pickup device	348/307	257/258; 257/263; 348/216.1	Nishizawa; Jun-ichi et al.
US 4589003	19860513	Solid state image sensor	257/258	257/262;	Yamada;

A		comprising photoelectric converting film and reading-out transistor		257/293; 257/E27.141; 257/E27.148	Hidetoshi et al.
US 4587562 A	19860506	Solid state image pick-up device	348/307	257/258; 257/263; 257/E27.148	Imai; Masaharu et al.
US 4574310 A	19860304	One-dimensional semiconductor imaging device	348/307	257/114; 257/136; 257/E27.148	Nishizawa; Jun-ichi et al.
US 4572763 A	19860225	Method and apparatus for performing epitaxial growth of ZnSe crystal from a melt thereof	117/59	117/64; 117/900; 117/906	Nishizawa; Jun-ichi
US 4571727 A	19860218	Far-infrared electromagnetic wave generator	372/4	372/50.11	Nishizawa; Jun-ichi et al.
US 4571624 A	19860218	Two-dimensional solid-state image sensor device	348/307	257/258; 257/263; 257/514	Nishizawa; Junichi et al.
US 4565156 A	19860121	Apparatus for performing solution growth relying on temperature difference technique	118/412	117/57; 117/61; 118/415; 118/425; 257/E21.114	Nishizawa; Jun-ichi et al.
US 4562474 A	19851231	Semiconductor image sensor	348/307	257/291; 257/E27.148	Nishizawa; Jun-ichi
US 4558660 A	19851217	Semiconductor fabricating apparatus	118/725	118/50.1; 219/411; 257/E21.349	Nishizawa; Jun-ichi et al.
US 4540466 A	19850910	Method of fabricating semiconductor device by dry process utilizing photochemical reaction, and apparatus therefor	438/708	118/50.1; 118/620; 118/728; 156/345.5; 204/192.25; 204/298.31; 204/298.33; 257/E21.101; 257/E21.214; 257/E21.252; 257/E21.279; 257/E21.292; 257/E21.347; 257/E21.349; 427/527; 427/586; 427/596; 438/758;	Nishizawa; Jun-ichi

				438/778	
US 4536946 A	19850827	Method for fabricating semiconductor photodetector	438/57	257/E27.131; 257/E27.148; 257/E29.059; 438/193; 438/73	Nishizawa; Junichi et al.
US 4534033 A	19850806	Three terminal semiconductor laser	372/50.1	257/136; 372/46.01	Nishizawa; Jun-ichi et al.
US 4531156 A	19850723	Solid state image pickup device	348/307	257/258; 257/E27.148; 348/296	Nishizawa; Jun-ichi et al.
US 4526632 A	19850702	Method of fabricating a semiconductor pn junction	438/501	252/62.3ZT; 257/614; 257/78; 257/E21.464; 257/E21.465; 257/E21.467; 257/E21.468; 257/E21.47; 257/E29.098; 438/22; 438/502	Nishizawa; Jun-ichi et al.
US 4525742 A	19850625	Two-dimensional solid-state image sensor device	348/307	257/258; 257/263; 257/E27.148; 257/E31.079	Nishizawa; Junichi et al.
US 4524391 A	19850618	Two-dimensional solid-state image sensor device	348/307	257/258; 257/263; 257/E27.148	Nishizawa; Junichi et al.
US 4506281 A	19850319	GaAs semiconductor device	257/264	257/273; 257/E21.268; 257/E21.697; 257/E29.194	Nishizawa; Jun-ichi et al.
US 4504865 A	19850312	Image signal readout method for solid-state image sensor	348/281	257/292; 257/443	Nishizawa; Jun-ichi et al.
US 4504847 A	19850312	Static induction type semiconductor device	257/264	257/136; 257/266; 257/285; 257/E29.049; 257/E29.196; 257/E29.243	Nishizawa; Jun-ichi
US 4502203 A	19850305	Method for fabricating semiconductor photodetector	438/57	257/258; 257/443; 257/E27.131; 257/E27.148; 438/195;	Nishizawa; Junichi et al.

				438/98	
US 4499654 A	19850219	Method for fabricating semiconductor photodetector	438/57	257/113; 257/443; 257/E27.131; 257/E27.148; 438/195; 438/196; 438/98	Nishizawa; Junichi et al.
US 4484207 A	19841120	Static induction transistor and semiconductor integrated circuit using hetero-junction	257/192	257/183; 257/200; 257/264; 257/51; 257/E29.091; 257/E29.14; 257/E29.194	Nishizawa; Jun-ichi et al.
US 4482910 A	19841113	Heterojunction emitter transistor with saturation drift velocity gradient in base	257/26	257/198; 257/592; 257/E29.085; 257/E29.241	Nishizawa; Jun-ichi et al.
US 4475131 A	19841002	Image storage device	386/117	257/E27.128; 348/211.99; 358/906	Nishizawa; Jun-ichi et al.
US 4472638 A	19840918	Two-dimensional solid-state image sensor	348/309	250/208.1; 257/E27.148; 348/308	Nishizawa; Jun-ichi et al.
US 4471228 A	19840911	Solid-state image sensor with exposure controller	348/298	250/208.1; 257/E27.148; 348/362; 356/222; 356/406	Nishizawa; Jun-ichi et al.
US 4470059 A	19840904	Gallium arsenide static induction transistor	257/264	257/266; 257/279; 257/E29.021; 257/E29.059; 257/E29.089; 257/E29.194; 257/E29.243	Nishizawa; Jun-ichi et al.
US 4465527 A	19840814	Method for producing a group IIB-VIB compound semiconductor crystal	117/79	117/61; 117/83; 117/939; 117/956; 117/958	Nishizawa; Jun-ichi
US 4454526 A	19840612	Semiconductor image sensor and the method of operating the same	257/292	257/184; 257/258; 257/E27.148	Nishizawa; Jun-ichi et al.
US 4450468	19840522	Gallium arsenide ISL gate	257/264	257/497;	Nishizawa;

A		with punched-through bipolar driver transistor		257/575; 326/109; 326/114	Junichi et al.
US 4450466 A	19840522	Semiconductor image sensor	257/292	257/E21.557; 257/E27.148; 257/E31.07	Nishizawa; Jun-ichi et al.
US 4436770 A	19840313	Oxynitride film and its manufacturing method	427/570	204/192.15; 257/E21.269; 257/E29.162; 257/E29.345; 427/162; 427/255.29; 427/255.34; 427/255.394; 427/96.8; 438/779; 438/784	Nishizawa; Jun-ichi et al.
US 4434433 A	19840228	Enhancement mode JFET dynamic memory	257/264	257/298; 257/306; 257/316; 257/E27.075; 257/E29.243; 365/149; 365/185.01	Nishizawa; Jun-ichi
US 4427990 A	19840124	Semiconductor photo-electric converter with insulated gate over p-n charge storage region	257/258	257/260; 257/264; 257/E27.148; 257/E31.079	Nishizawa; Jun-ichi
US 4425143 A	19840110	Adsorption by zeolitic composition	95/126	422/169; 423/219; 423/351; 95/138; 96/146	Nishizawa; Junichi et al.
US 4416952 A	19831122	Oxynitride film and its manufacturing method	428/698	148/33.3; 204/192.26; 257/411; 257/E21.269; 257/E29.162; 257/E29.345; 423/353; 423/392; 428/469; 428/697; 428/701; 428/702	Nishizawa; Jun-ichi et al.
US 4415937	19831115	Solid-state image storage	386/117	257/E27.148;	Nishizawa;

A		device		358/906	Jun-ichi et al.
US 4414558 A	19831108	Hetero-junction light-emitting diode	257/96	257/E33.043; 257/E33.049; 372/50.1	Nishizawa; Jun-ichi et al.
US 4408304 A	19831004	Semiconductor memory	365/174	257/306; 257/378; 257/E27.084; 365/243	Nishizawa; Jun-ichi et al.
US 4404575 A	19830913	Semiconductor device	257/264	257/247; 257/E29.021; 257/E29.165; 257/E29.194; 257/E29.243	Nishizawa; Jun-ichi
US 4400710 A	19830823	Semiconductor device	257/136	12/22; 12/38; 257/155; 257/264; 257/474; 257/E29.194; 257/E29.196; 257/E29.271; 257/E29.31; 257/E29.311	Nishizawa; Jun-ichi et al.
US 4389256 A	19830621	Method of manufacturing pn junction in group II-VI compound semiconductor	438/45	117/2; 257/E21.467; 257/E21.468; 257/E21.47; 257/E29.098; 438/501; 438/537; 438/796; 438/971	Nishizawa; Jun-ichi et al.
US 4377817 A	19830322	Semiconductor image sensors	257/258	257/264; 257/447; 257/E27.148; 257/E31.079	Nishizawa; Jun-ichi et al.
US 4371412 A	19830201	Dry etching apparatus	156/345.45	118/723I; 204/298.34; 204/298.39; 216/67; 216/71	Nishizawa; Junichi
US 4365262 A	19821221	Semiconductor image sensor	257/258	257/E27.148	Nishizawa; Junichi
US 4364072 A	19821214	Static induction type semiconductor device with multiple doped layers for potential modification	257/264	257/136; 257/266; 257/285; 257/E29.049;	Nishizawa; Jun-ichi

				257/E29.196; 257/E29.243	
US 4359012 A	19821116	Apparatus for producing a semiconductor device utilizing successive liquid growth	118/59	118/412; 118/415	Nishizawa; Jun-ichi
US 4354140 A	19821012	Light-emitting semiconductor	313/499	257/185; 257/E33.045; 257/E33.049	Nishizawa; Jun-ichi
US 4347097 A	19820831	Method and apparatus for producing a multilayer semiconductor device utilizing liquid growth	117/57	117/67; 117/954; 118/412; 422/253	Nishizawa; Jun-ichi
US 4346513 A	19820831	Method of fabricating semiconductor integrated circuit device utilizing selective etching and epitaxial refill	438/187	117/902; 257/515; 257/521; 257/E21.09; 257/E21.123; 257/E21.223; 257/E21.231; 257/E21.54; 257/E21.56; 438/192; 438/357; 438/401; 438/418; 438/975	Nishizawa; Junichi et al.
US 4340827 A	19820720	Semiconductor integrated circuit	326/100	257/273; 257/575; 326/109	Nishizawa; Jun-ichi et al.
US 4338618 A	19820706	Composite static induction transistor and integrated circuit utilizing same	257/264	257/273; 257/E27.032; 257/E27.069; 257/E29.194	Nishizawa; Jun-ichi
US 4337473 A	19820629	Junction field effect transistor having unsaturated drain current characteristic with lightly doped drain region	257/264	257/266; 257/E29.059; 257/E29.243	Nishizawa; Jun-ichi
US 4334235 A	19820608	Insulated gate type semiconductor device	257/344	257/331; 257/345; 257/E29.04; 257/E29.051; 257/E29.133; 257/E29.243	Nishizawa; Jun-ichi
US 4333989	19820608	Sapphire single crystal	428/446	257/E21.121;	Nishizawa;

A		substrate consisting essentially of Ga.sub.2 O.sub. 3		428/700; 501/153; 501/86	Jun-Ichi et al.
US 4331737 A	19820525	Oxynitride film and its manufacturing method	428/457	148/33.3; 257/435; 257/E21.269; 257/E29.162; 257/E29.345; 428/689; 428/697; 428/698; 428/702; 438/779; 438/958	Nishizawa; Jun-ichi et al.
US 4329625 A	19820511	Light-responsive light-emitting diode display	315/158	257/257; 257/261; 257/264; 257/266; 257/82; 257/E31.079; 257/E33.076; 315/152; 315/192; 315/311; 315/312; 315/53; 327/109; 327/514; 362/800	Nishizawa; Jun-ichi et al.
US 4326209 A	19820420	Static induction transistor	257/264	257/268; 257/284; 257/E29.243	Nishizawa; Jun-ichi et al.
US 4320410 A	19820316	GaAs Semiconductor device	257/264	257/273; 257/E21.268; 257/E21.697; 257/E29.194	Nishizawa; Jun-ichi et al.
US 4317127 A	19820223	Static induction transistor and integrated circuit utilizing same	257/264	148/DIG.85; 148/DIG.87; 257/273; 257/289; 257/471; 257/E29.194; 326/100; 326/131	Nishizawa; Jun-ichi
US 4315796 A	19820216	Crystal growth of compound semiconductor mixed	117/57	117/61; 117/64;	Nishizawa; Jun-ichi

		crystals under controlled vapor pressure		117/67; 117/906; 117/912; 117/953; 117/954; 117/955; 117/956; 148/DIG.6	
US 4300151 A	19811110	Change transfer device with PN Junction gates	257/217	257/216; 257/E29.228; 377/58; 377/62	Nishizawa; Jun-ichi
US 4297718 A	19811027	Vertical type field effect transistor	257/259	257/266; 257/E29.313	Nishizawa; Jun-Ichi et al.
US 4296425 A	19811020	Luminescent diode having multiple hetero junctions	257/96	257/773; 257/E21.117; 438/47	Nishizawa; Jun-ichi
US 4292374 A	19810929	Sapphire single crystal substrate for semiconductor devices	428/446	117/902; 148/33; 148/DIG.150; 148/DIG.72; 148/DIG.79; 148/DIG.97; 257/E21.121; 428/697; 428/700; 501/86	Nishizawa; Jun-ichi et al.
US 4292373 A	19810929	Sapphire single crystal substrate for semiconductor devices	428/446	117/902; 148/33; 148/DIG.150; 148/DIG.72; 148/DIG.97; 257/E21.121; 428/697; 428/700; 501/86	Nishizawa; Jun-ichi et al.
US 4284997 A	19810818	Static induction transistor and its applied devices	257/264	257/262; 257/270; 257/273; 257/386; 257/498; 257/E29.194; 257/E29.243; 326/100; 326/101	Nishizawa; Jun-ichi
US 4271408	19810602	Colored-light emitting	345/83	340/815.45;	Teshima; Toru

A		display		340/815.56; 340/815.75; 345/697; 362/240; 362/293; 362/800; 362/812; 40/564; 40/581	et al.
US 4270059 A	19810526	Static induction transistor logic circuit	326/100	257/264; 257/273; 257/E27.032; 257/E27.069; 257/E29.194; 326/109	Nishizawa; Jun-ichi et al.
US 4266238 A	19810505	Semiconductor device having high-speed operation and integrated circuit using same	257/544	257/264; 257/335; 257/386; 257/552; 257/E27.031; 257/E29.034; 257/E29.062; 257/E29.063; 257/E29.243; 326/101	Nishizawa; Jun-ichi
US 4259681 A	19810331	Integrated circuit	257/264	148/DIG.168; 148/DIG.50; 148/DIG.51; 257/273; 257/E21.608; 257/E27.032; 257/E27.069; 257/E29.194; 326/100; 326/101; 326/17	Nishizawa; Jun-ichi
US 4233109 A	19801111	Dry etching method	216/67	118/723I; 204/164; 204/192.34; 204/298.39; 422/186.05; 438/711; 438/712; 438/730; 438/732	Nishizawa; Junichi
US 4216038	19800805	Semiconductor device and	438/189	257/264;	Nishizawa;

A		manufacturing process thereof		257/273; 257/285; 257/E21.033; 257/E29.194; 438/192; 438/193; 438/545; 438/552; 438/942	Jun-ichi et al.
US 4199771 A	19800422	Static induction transistor	257/264	257/266; 257/E29.243; 438/192; 438/193	Nishizawa; Jun-Ichi et al.
US 4198648 A	19800415	Integrated semiconductor device	257/264	257/273; 257/E27.032; 257/E27.069; 257/E29.194; 326/100	Nishizawa; Jun-ichi
US 4198645 A	19800415	Semiconductor controlled rectifier having gate grid dividing surrounding zone into two different impurity concentration sections	257/136	257/155; 257/264; 257/266; 257/270; 257/E29.196	Nishizawa; Jun-ichi
US 4177321 A	19791204	Single crystal of semiconductive material on crystal of insulating material	428/446	117/101; 156/78; 257/E21.121; 428/428; 428/432; 428/700; 438/967	Nishizawa; Jun-ichi
US 4171995 A	19791023	Epitaxial deposition process for producing an electrostatic induction type thyristor	438/137	148/DIG.88; 257/136; 257/E21.362; 257/E29.196; 438/499; 438/505	Nishizawa; Jun-ichi et al.
US 4160259 A	19790703	Semiconductor device	257/264	257/268; 257/270; 257/E29.022; 257/E29.059; 257/E29.243; 257/E29.264; 257/E29.265; 257/E29.312; 257/E29.313; 257/E29.319;	Nishizawa; Jun-ichi

				327/574	
US RE29971 E	19790417	Field effect semiconductor device having an unsaturated triode vacuum tube characteristic	257/264	257/403; 257/E29.243	Nishizawa; Jun-ichi et al.
US 4126731 A	19781121	Sapphire single crystal substrate for semiconductor devices	428/446	117/902; 257/E21.121; 423/600; 428/700; 501/153; 501/86	Nishizawa; Jun-ichi et al.
US 4115793 A	19780919	Field effect transistor with reduced series resistance	257/266	148/DIG.88; 257/286; 257/E29.039; 257/E29.059; 438/173; 438/193	Nishizawa; Jun-ichi
US 4086611 A	19780425	Static induction type thyristor	257/136	148/DIG.88; 257/145; 257/E29.196	Nishizawa; Jun-ichi et al.
US 4038610 A	19770726	Luminosity control system employing semiconductor lasers	372/8	359/336; 359/344; 372/46.01; 372/50.1	Nishizawa; Jun-ichi et al.
US 3990902 A	19761109	Magnesium-titanate-comprising spinel single crystal substrate for semiconductor devices	501/134	257/E21.121; 501/153	Nishizawa; Jun-ichi et al.
US 3986060 A	19761012	Compound transistor circuitry	327/581	330/207P; 330/277; 330/298; 361/58; 361/98	Nishizawa; Jun-ichi et al.
US 3947548 A	19760330	Process of growing single crystals of gallium phosphide	117/3	117/67; 117/79; 117/955; 423/305	Nishizawa; Jun-Ichi et al.
US 3946270 A	19760323	Signal collecting and distributing systems	348/800	257/E27.133	Nishizawa; Jun-ichi et al.
US 3896484 A	19750722	Intrinsic semiconductor charge transfer device using alternate transfer of electrons and holes	257/215	257/218; 257/912; 257/E29.058; 257/E29.065; 257/E29.239; 327/581	Nishizawa; Jun-ichi et al.
US 3889164	19750610	Position control system	318/640	318/577;	Nishizawa;

A		using magnetic forces for correcting the inclination of a controlled member including a torsional mounting		318/594; 318/603; 318/687; 356/500; 356/510	Junichi et al.
US 3883862 A	19750513	Signal collecting and distributing systems	345/80	250/553	Nishizawa; Jun-Ichi et al.
US 3880677 A	19750429	Method for producing a single crystal of In.sub.x Ga.sub.1.sub.-x P	117/3	117/79; 117/955; 252/62.3GA; 420/555	Nishizawa; Jun-Ichi et al.
US 3871764 A	19750318	Pattern generator apparatus	355/18	355/40; 396/548	Nishizawa; Junichi
US 3836999 A	19740917	SEMICONDUCTOR WITH GROWN LAYER RELIEVED IN LATTICE STRAIN	148/33	148/DIG.40; 148/DIG.67; 148/DIG.72; 148/DIG.97; 257/607; 257/655; 257/E21.102; 257/E29.086; 438/938	Nishizawa; Jun-Ichi
US 3829885 A	19740813	CHARGE COUPLED SEMICONDUCTOR MEMORY DEVICE	257/215	257/227; 257/E29.058; 257/E29.239; 327/581	Nishizawa; Junichi et al.
US 3828230 A	19740806	FIELD EFFECT SEMICONDUCTOR DEVICE HAVING AN UNSATURATED TRIODE VACUUM TUBE CHARACTERISTI	257/264	148/DIG.145; 148/DIG.53; 257/327; 257/365; 257/E29.243	Nishizawa; Jun-Ichi et al.
US 3809953 A	19740507	METHOD OF AND DEVICE FOR CONTROLLING OPTICAL CONVERSION IN SEMICONDUCTOR	359/321	257/E27.129; 257/E31.114	Nishizawa; Jun-Ichi
US 3793093 A	19740219	METHOD FOR PRODUCING A SEMICONDUCTOR DEVICE HAVING A VERY SMALL DEVIATION IN LATTICE CONSTANT	438/546	148/DIG.18; 148/DIG.40; 148/DIG.56; 148/DIG.61; 148/DIG.65; 148/DIG.97; 252/62.3GA; 257/E29.086; 257/E29.093;	Nishizawa; Junichi et al.

				438/547; 438/569; 438/938	
US 3789317 A	19740129	SIGNAL CONVERTER WHEREIN PHOTOEMISSION TIME CONSTANT IS UTILIZED	372/8	257/461; 257/80; 359/336	Nishizawa; Junichi
US 3789285 A	19740129	POSITION CONTROL SYSTEM USING MAGNETIC FORCE	318/687	310/12; 318/594; 318/640; 318/676; 335/268	Nishizawa; Junichi
US 3762367 A	19731002	GROWTH APPARATUS FOR A LIQUID GROWTH MULTI-LAYER FILM	118/422	117/57; 118/423; 257/E21.117	Nishizawa; Junichi et al.
US 3760201 A	19730918	OPTICAL FLIP-FLOP ELEMENT	372/8	327/187; 372/49.01	Nishizawa; Jun-ichi et al.
US 3634849 A	19720111	SIGNAL COLLECTING AND DISTRIBUTING SYSTEMS	250/214R	257/E27.133; 333/217	Nishizawa; Jun-Ichi et al.
US 3633059 A	19720104	ELECTROLUMINESCENT PN JUNCTION SEMICONDUCTOR DEVICE FOR USE AT HIGHER FREQUENCIES	313/499	257/101; 257/610	Nishizawa; Jun-ichi et al.
US 3614197 A	19711019	SOLID OPTICAL WAVE GUIDE HAVING A RADIALLY VARYING REFRACTIVE INDEX	385/124	250/227.28; 65/30.1; 65/37; 65/60.8	Nishizawa; Jun-ichi et al.
US 3602840 A	19710831	TRANSIT TIME DIODE OSCILLATOR USING TUNNEL INJECTION	331/96	257/604; 257/656; 257/657; 331/107DP; 331/107R; 331/107T	Nishizawa; Jun-ichi et al.
US 3538352 A	19701103	VARIABLE IMPEDANCE ACTIVE PULSE TRANSMISSION SYSTEM [TEXT AVAILABLE IN USOCR DATABASE]	327/177	327/195; 327/514	NISHIZAWA JUN-ICHI
US 3493823 A	19700203	NEGATIVE-RESISTANCE SEMICONDUCTOR DEVICE FOR HIGH FREQUENCIES [TEXT AVAILABLE IN USOCR	257/480	257/482; 257/595; 257/604	NISHIZAWA JUNICHI et al.

		DATABASE				
--	--	----------	--	--	--	--